

**FC903**

Silicon Epitaxial Planar Type

High-Speed Switching Composite Diode

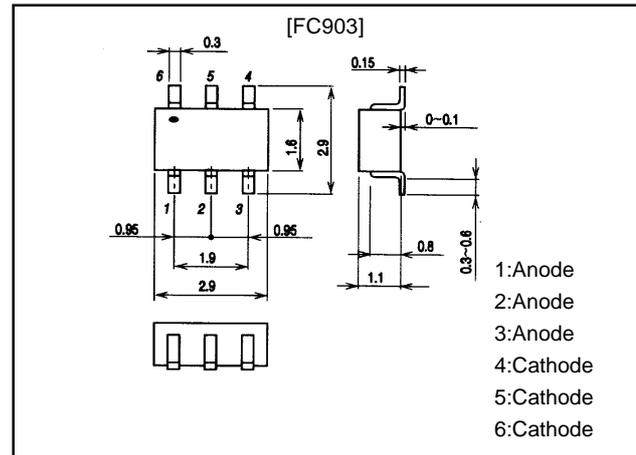
Features

- Composite type with 3 diodes contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC903 is formed with 3 chips, each being equivalent to the DSB010, placed in one package.
- High switching speed.

Package Dimensions

unit:mm

1288



Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|-----------|-------------|-------------|------|
| Peak Reverse Voltage | V_{RM} | | 85 | V |
| Reverse Voltage | V_R | | 80 | V |
| Peak Forward Current | I_{FM} | | 300 | mA |
| Average Rectified Current | I_O | | 100 | mA |
| Surge Forward Current | I_{FSM} | 1μs | 4 | A |
| Allowable Power Dissipation | P | Total value | 300 | mW |
| Junction Temperature | T_J | | 125 | °C |
| Storage Temperature | T_{stg} | | -55 to +125 | °C |

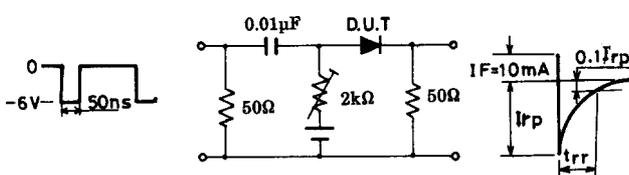
Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---------------------------|----------|--|---------|------|-----|------|
| | | | min | typ | max | |
| Forward Voltage | V_{F1} | $I_F=1mA$ | | 0.60 | | V |
| | V_{F2} | $I_F=10mA$ | | 0.72 | | V |
| | V_{F3} | $I_F=100mA$ | | | 1.2 | V |
| Reverse Current | I_{R1} | $V_R=30V$ | | | 0.1 | μA |
| | I_{R2} | $V_R=80V$ | | | 0.5 | μA |
| Interterminal Capacitance | C | $V_R=0V, f=1MHz$ | | | 3.0 | pF |
| Reverse Recovery Time | t_{rr} | $I_F=10mA, V_R=6V, R_L=50\Omega, I_{rr}=0.1I_{rp}$ | | | 4.0 | ns |

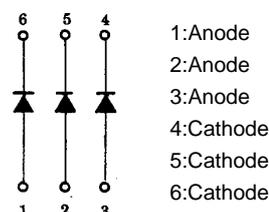
Note: The specifications shown above are for each individual diode.

Marking : 903

t_{rr} Test Circuit

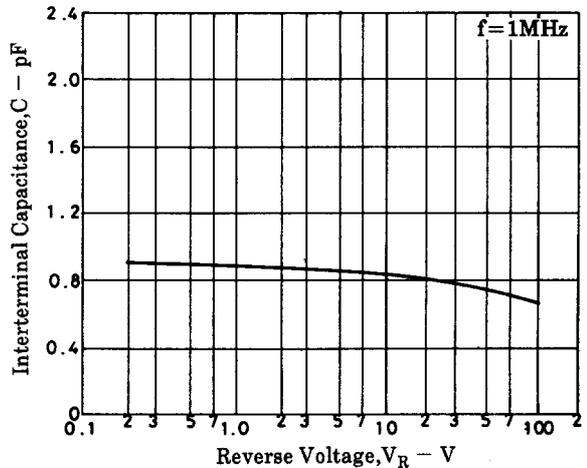
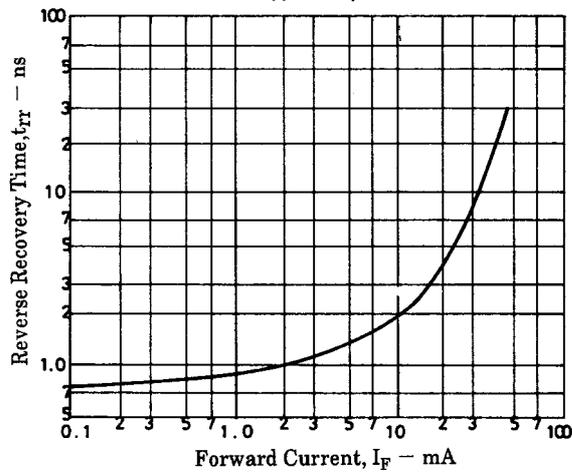
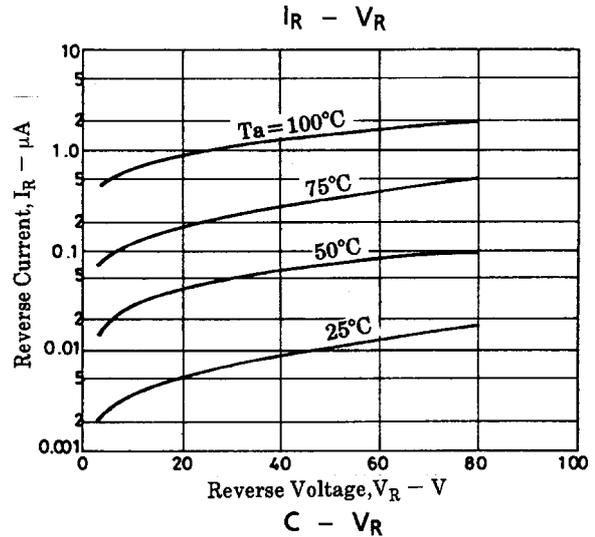
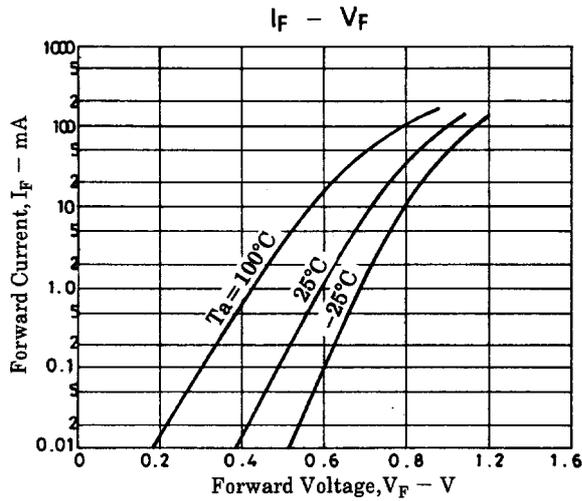


Electrical Connection



SANYO Electric Co., Ltd. Semiconductor Business Headquarters
 TOKYO OFFICE, Tokyo Bldg., 1-10, Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

FC903



- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
 - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use;
 - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of June, 1998. Specifications and information herein are subject to change without notice.